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Quad. 2-input OR Gates



ADE-205-243A (Z)

2nd. Edition Jul. 2001

Description

The HD74LV32A has four two-input OR gates in a 14-pin package.

Low-voltage and high-speed operation is suitable for the battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

Features

- $V_{cc} = 2.0 \text{ V to } 5.5 \text{ V operation}$
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@ V_{cc} = 0 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.3 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Output current $\pm 6 \text{ mA}$ (@V_{cc} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{cc} = 4.5 V to 5.5 V)

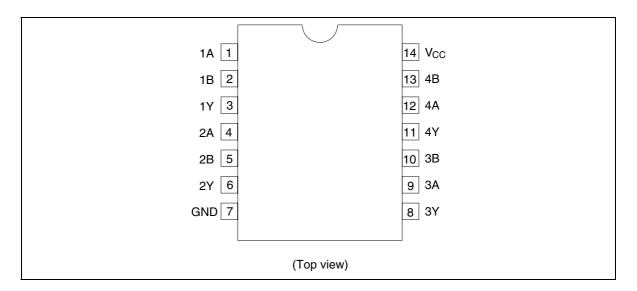
Function Table

Inputs

Α	В	Output Y
Н	Х	Н
X	Н	Н
L	L	L

Note: H: High level
L: Low level
X: Immaterial

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range*1	V,	-0.5 to 7.0	V	
Output voltage range*1,2	V _o	-0.5 to $V_{cc} + 0.5$	V	Output: H or L
		-0.5 to 7.0	_	V _{cc} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_o < 0 \text{ or } V_o > V_{cc}$
Continuous output current	I _o	±25	mA	$V_o = 0$ to V_{cc}
Continuous current through V _{cc} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	785	mW	SOP
		500	_	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not be exceeded however briefly. In addition, two or more items must not reach their limit values at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	2.0	5.5	V	
Input voltage range	V _i	0	5.5	V	
Output voltage range	V _o	0	V _{cc}	V	
Output current	I _{OH}	_	-50	μΑ	$V_{cc} = 2.0 \text{ V}$
		_	-2	mA	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		_	-6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	-12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
	I _{OL}	_	50	μΑ	V _{cc} = 2.0 V
		_	2	mA	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		_	6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Input transition rise or fall rate	Δt/Δν	0	200	ns/V	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		0	100		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Logic Diagram

DC Electrical Characteristics

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$

Item	Symbol	$V_{cc}(V)^*$	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.0	1.5	_	_	٧	
		2.3 to 2.7	$V_{cc} \times 0.7$	_	_	_	
		3.0 to 3.6	$V_{cc} \times 0.7$	_	_	_	
		4.5 to 5.5	$V_{cc} \times 0.7$	_	_	_	
	V _{IL}	2.0	_	_	0.5	_	
		2.3 to 2.7	_	_	$V_{cc} \times 0.3$	_	
		3.0 to 3.6	_	_	$V_{cc} \times 0.3$	_	
		4.5 to 5.5	_	_	$V_{cc} \times 0.3$	_	
Output voltage	V _{OH}	Min to Max	V _{cc} - 0.1	_	_	V	$I_{OH} = -50 \mu A$
		2.3	2.0	_	_	_	I _{OH} = -2 mA
		3.0	2.48	_	_		I _{OH} = -6 mA
		4.5	3.8	_	_	_	I _{OH} = -12 mA
	V _{oL}	Min to Max	_	_	0.1	_	Ι _{οι} = 50 μΑ
		2.3	_	_	0.4	_	I _{OL} = 2 mA
		3.0	_	_	0.44	_	I _{oL} = 6 mA
		4.5	_	_	0.55	_	I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	I _{cc}	5.5	_	_	20	μА	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
Output leakage current	OFF	0	_	_	5	μΑ	$V_{_{\rm I}}$ or $V_{_{\rm O}}$ = 0 V to 5.5 V
Input capacitance	C _{IN}	3.3	_	3.3	_	pF	$V_{_{I}} = V_{_{CC}}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $V_{cc} = 2.5 \pm 0.2 \text{ V}$

		1a = 1	25°C		1a = - 85°C	-40 to				
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t _{PLH}	_	7.1	12.8	1.0	15.0	ns	C _L = 15 pF	A or B	Υ
delay time	$\mathbf{t}_{_{\mathrm{PHL}}}$	_	9.6	16.2	1.0	19.0		C _L = 50 pF	•	

 $V_{cc} = 3.3 \pm 0.3 \text{ V}$

		Ta = 1	25°C		Ta = - 85°C	40 to	_			
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t _{PLH}	_	5.0	7.9	1.0	9.5	ns	C _L = 15 pF	A or B	Υ
delay time	$t_{\scriptscriptstylePHL}$	_	6.9	11.4	1.0	13.0	=	C _L = 50 pF	•	

 $V_{cc} = 5.0 \pm 0.5 \text{ V}$

		Ta = 1	25°C		Ta = 85°C	40 to				
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t _{PLH}	_	3.6	5.5	1.0	6.5	ns	C _L = 15 pF	A or B	Υ
delay time	t _{PHL}	_	4.9	7.5	1.0	8.5		C _L = 50 pF	-	

Operating Characteristics

 $C_L = 50 \text{ pF}$

Ta	_	250	
ıa	=	25	_

Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C_{\scriptscriptstylePD}	3.3	_	9.5	_	pF	f = 10 MHz
		5.0	_	11.5	_		

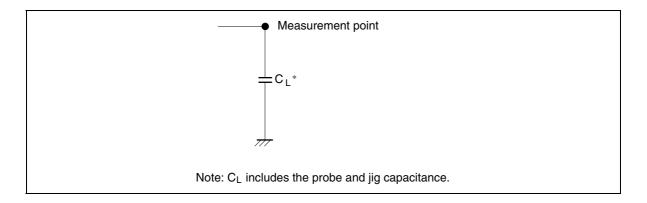
Noise Characteristics

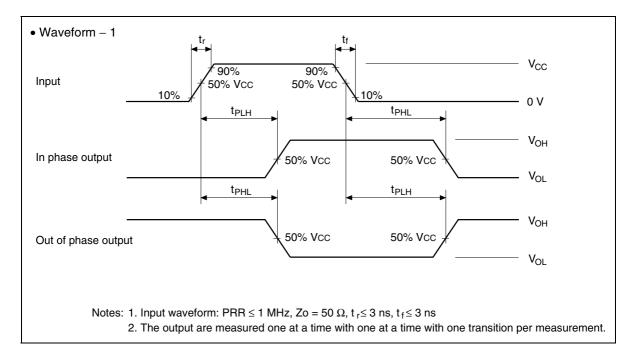
 $C_L = 50 \text{ pF}$

Ta = 25°

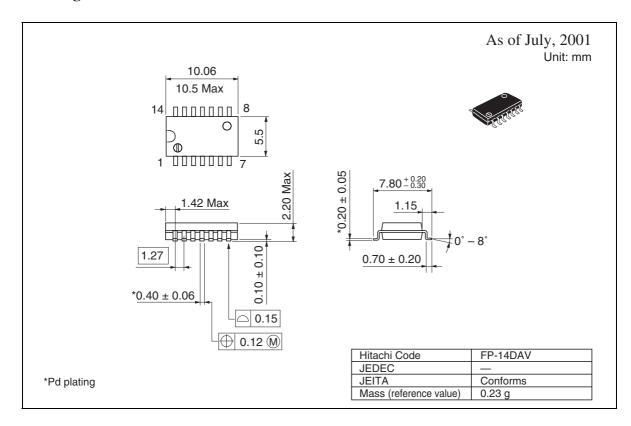
Item	Symbol	$V_{cc}(V)$	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V _{oL}	$V_{OL(P)}$	3.3	_	0.2	0.8	V	
Quiet output, minimum dynamic V _{oL}	V _{OL (V)}	3.3	_	-0.1	-0.8		
Quiet output, minimum dynamic V _{он}	V _{OH (V)}	3.3	_	3.1	_		
High-level dynamic input voltage	$V_{_{IH\;(D)}}$	3.3	2.31	_	_	V	
Low-level dynamic inout voltage	V _{IL (D)}	3.3	_	_	0.99		

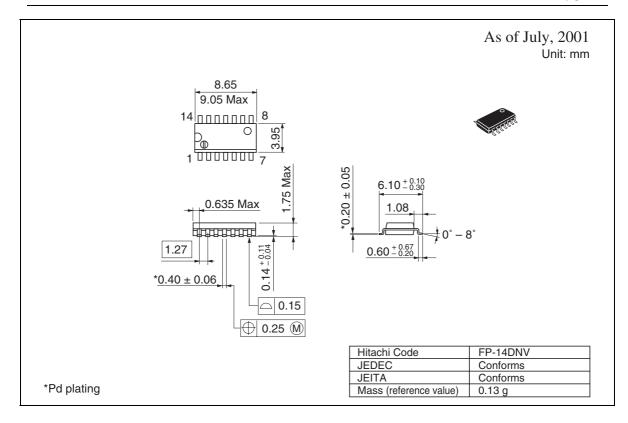
Test Circuit

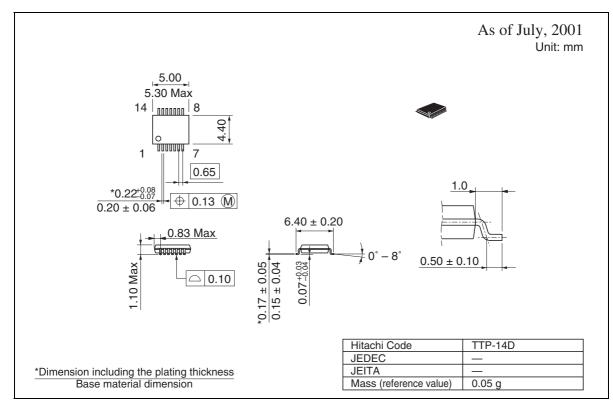




Package Dimensions







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